

NTGS3443, NVGS3443

Power MOSFET 4.4 Amps, 20 Volts

P-Channel TSOP-6

Features

- Ultra Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Miniature TSOP-6 Surface Mount Package
- These Devices are Pb-Free and are RoHS Compliant
- NVGS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	-20	Volts
Gate-to-Source Voltage – Continuous	V_{GS}	± 12	Volts
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	244	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	0.5	Watts
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$ – Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	I_D I_{DM}	-2.2 -10	Amps Amps
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	128	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	1.0	Watts
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$ – Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	I_D I_{DM}	-3.1 -14	Amps Amps
Thermal Resistance Junction-to-Ambient (Note 3)	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	2.0	Watts
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$ – Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	I_D I_{DM}	-4.4 -20	Amps Amps
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

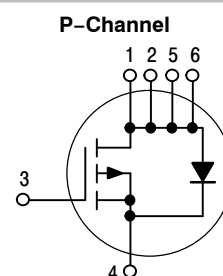
1. Minimum FR-4 or G-10 PCB, operating to steady state.
2. Mounted onto a 2 in square FR-4 board (1 in sq, 2 oz. Cu. 0.06" thick single sided), operating to steady state.
3. Mounted onto a 2 in square FR-4 board (1 in sq, 2 oz. Cu. 0.06" thick single sided), $t < 5.0$ seconds.



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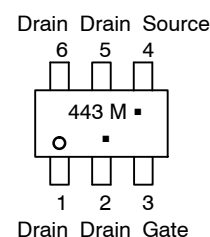
**4.4 AMPERES
20 VOLTS**
 $R_{DS(on)} = 65 \text{ m}\Omega$



MARKING DIAGRAM & PIN ASSIGNMENT



TSOP-6
CASE 318G
STYLE 1



443 = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTGS3443T1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel
NVGS3443T1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Notes 4 & 5)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = -10\text{ }\mu\text{A}$)	$V_{(BR)DSS}$	-20	-	-	Vdc
Zero Gate Voltage Drain Current ($V_{GS} = 0\text{ Vdc}$, $V_{DS} = -20\text{ Vdc}$, $T_J = 25^\circ\text{C}$) ($V_{GS} = 0\text{ Vdc}$, $V_{DS} = -20\text{ Vdc}$, $T_J = 70^\circ\text{C}$)	I_{DSS}	- -	- -	-1.0 -5.0	μAdc
Gate-Body Leakage Current ($V_{GS} = -12\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	-	-	-100	nAdc
Gate-Body Leakage Current ($V_{GS} = +12\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	-	-	100	nAdc

ON CHARACTERISTICS

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	-0.60	-0.95	-1.50	Vdc
Static Drain-Source On-State Resistance ($V_{GS} = -4.5\text{ Vdc}$, $I_D = -4.4\text{ Adc}$) ($V_{GS} = -2.7\text{ Vdc}$, $I_D = -3.7\text{ Adc}$) ($V_{GS} = -2.5\text{ Vdc}$, $I_D = -3.5\text{ Adc}$)	$R_{DS(on)}$	- - -	0.058 0.082 0.092	0.065 0.090 0.100	Ω
Forward Transconductance ($V_{DS} = -10\text{ Vdc}$, $I_D = -4.4\text{ Adc}$)	g_{FS}	-	8.8	-	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	$(V_{DS} = -5.0\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{iss}	-	565	-	pF
Output Capacitance		C_{oss}	-	320	-	pF
Reverse Transfer Capacitance		C_{rss}	-	120	-	pF

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$(V_{DD} = -20\text{ Vdc}$, $I_D = -1.0\text{ Adc}$, $V_{GS} = -4.5\text{ Vdc}$, $R_g = 6.0\text{ }\Omega$)	$t_{d(on)}$	-	10	25	ns
Rise Time		t_r	-	18	45	ns
Turn-Off Delay Time		$t_{d(off)}$	-	30	50	ns
Fall Time		t_f	-	31	50	ns
Total Gate Charge	$(V_{DS} = -10\text{ Vdc}$, $V_{GS} = -4.5\text{ Vdc}$, $I_D = -4.4\text{ Adc}$)	Q_{tot}	-	7.5	15	nC
Gate-Source Charge		Q_{gs}	-	1.4	-	nC
Gate-Drain Charge		Q_{gd}	-	2.9	-	nC

BODY-DRAIN DIODE RATINGS

Diode Forward On-Voltage	$(I_S = -1.7\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$)	V_{SD}	-	-0.83	-1.2	Vdc
Reverse Recovery Time	$(I_S = -1.7\text{ Adc}$, $dI_S/dt = 100\text{ A}/\mu\text{s}$)	t_{rr}	-	30	-	ns

- Indicates Pulse Test: P.W. = 300 μsec max, Duty Cycle = 2%.
- Handling precautions to protect against electrostatic discharge are mandatory.

TYPICAL ELECTRICAL CHARACTERISTICS

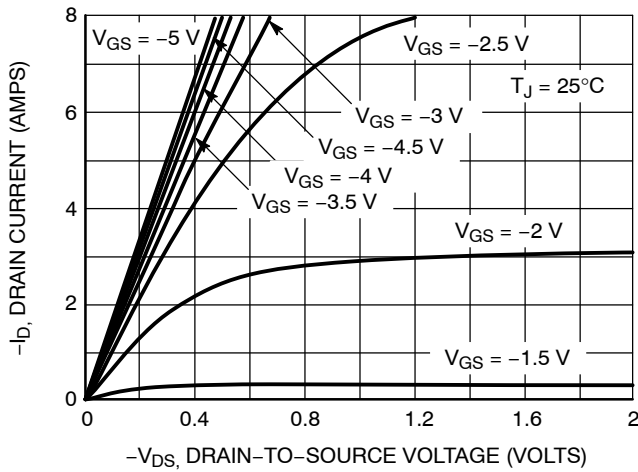


Figure 1. On-Region Characteristics

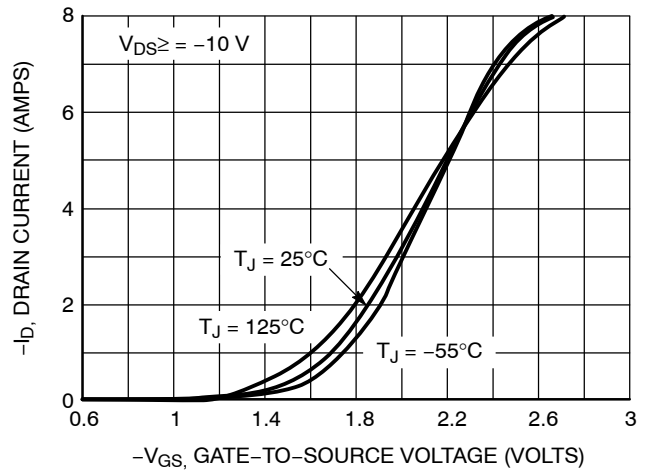


Figure 2. Transfer Characteristics

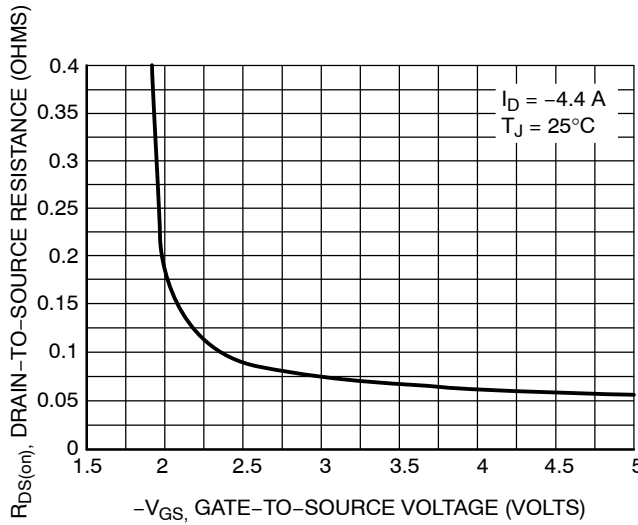


Figure 3. On-Resistance vs. Gate-to-Source Voltage

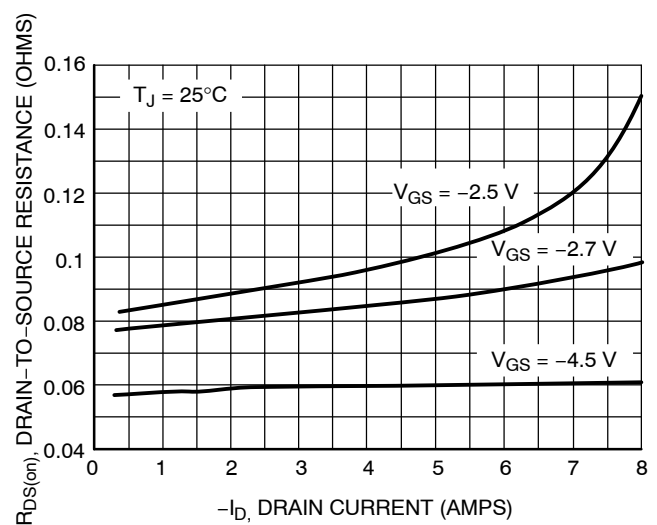


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

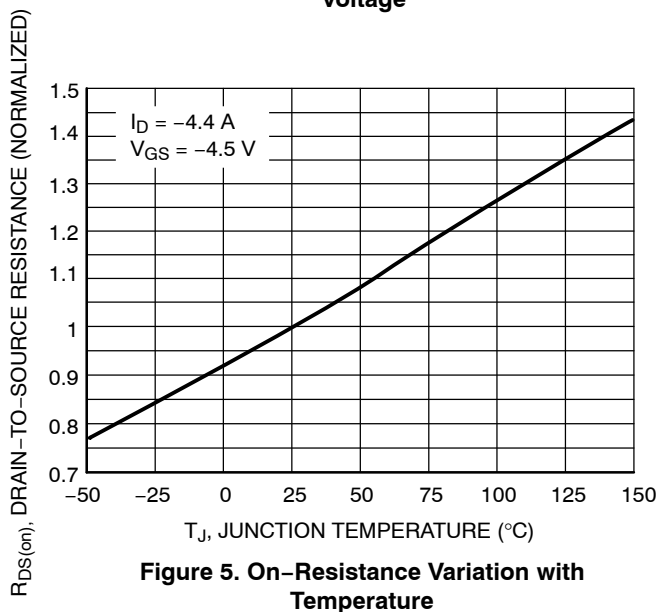


Figure 5. On-Resistance Variation with Temperature

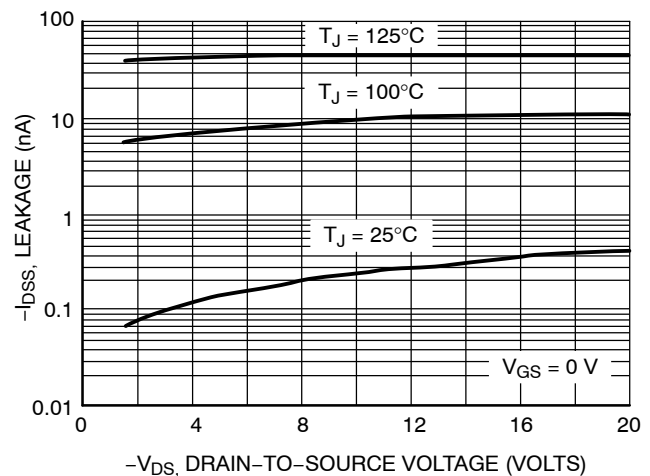


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL ELECTRICAL CHARACTERISTICS

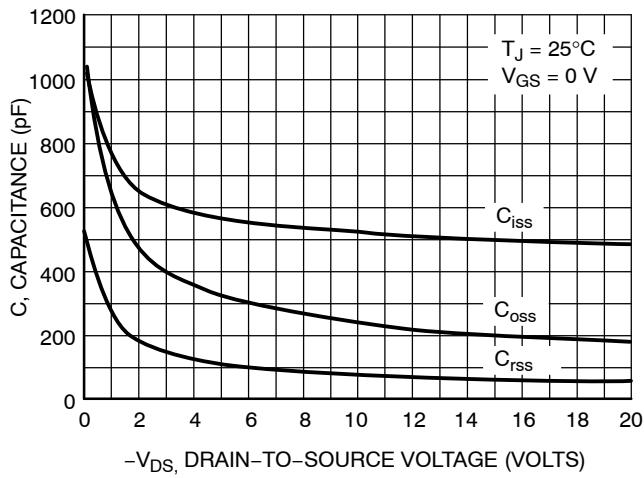


Figure 7. Capacitance Variation

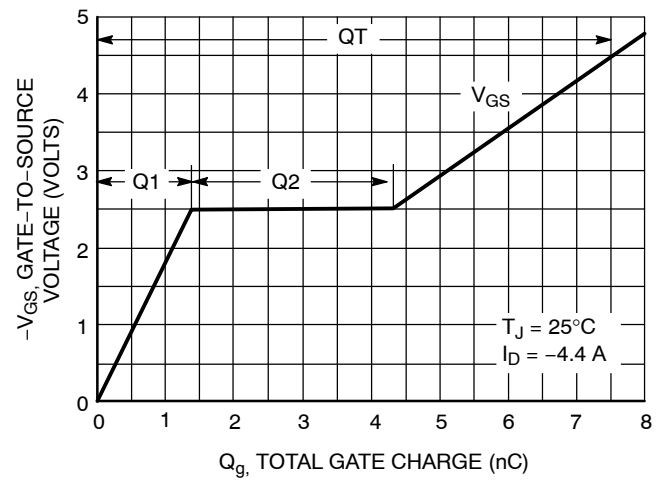


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

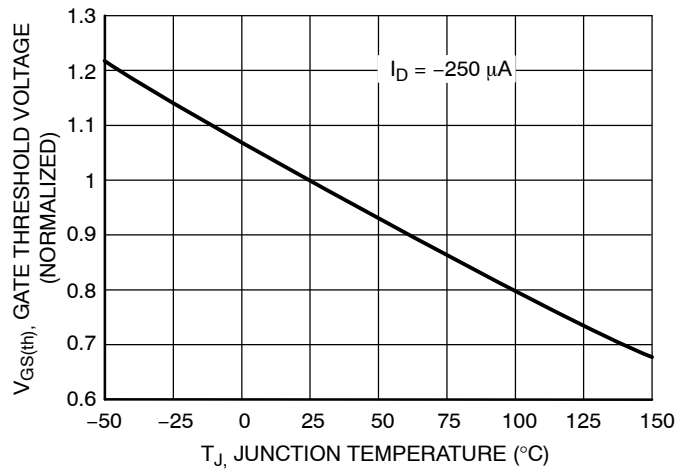


Figure 9. Gate Threshold Voltage Variation with Temperature

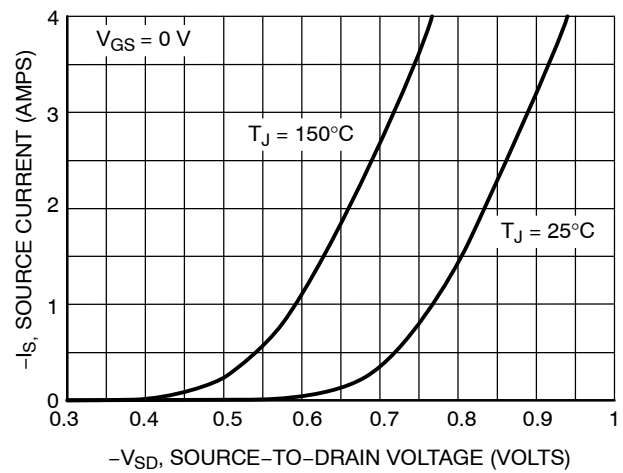


Figure 10. Diode Forward Voltage vs. Current

TYPICAL ELECTRICAL CHARACTERISTICS

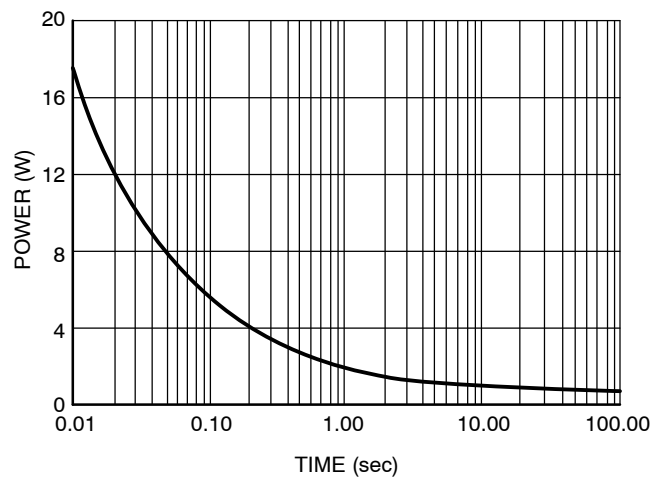


Figure 11. Single Pulse Power

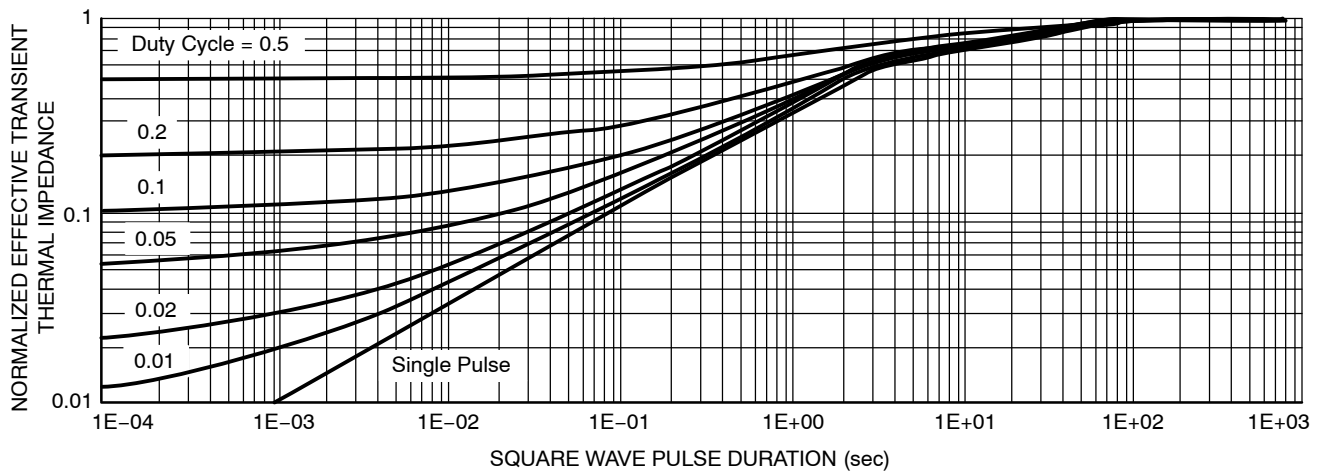


Figure 12. Normalized Thermal Transient Impedance, Junction-to-Ambient

NTGS3443T1/D



**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

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